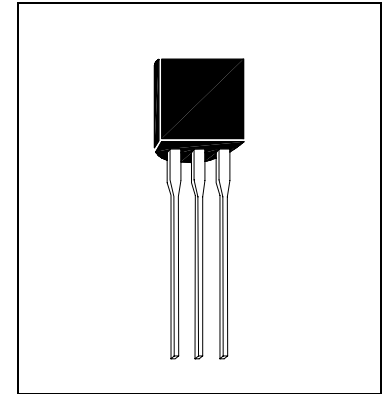




## 2SC1815

NPN EPITAXIAL PLANAR TRANSISTOR



### Description

The 2SC1815 is designed for use in driver stage of AF amplifier general purpose amplification.

### Absolute Maximum Ratings

- Maximum Temperatures  
Storage Temperature ..... -55~+150°C  
Junction Temperature ..... +150°C Maximum
- Maximum Power Dissipation  
Total Power Dissipation (Ta=25°C) ..... 400 mW
- Maximum Voltages and Currents (Ta=25°C)  
VCBO Collector to Base Voltage ..... 50 V  
VCEO Collector to Emitter Voltage ..... 50 V  
VEBO Emitter to Base Voltage ..... 5 V  
IC Collector Current ..... 150 mA

### Characteristics (Ta=25°C)

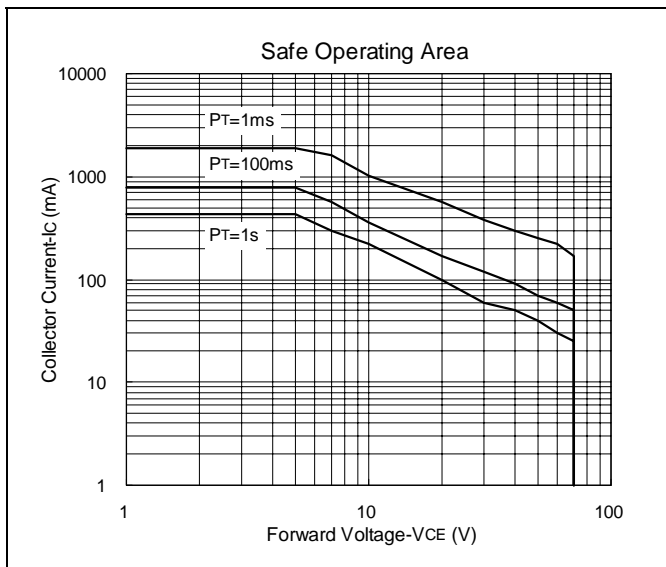
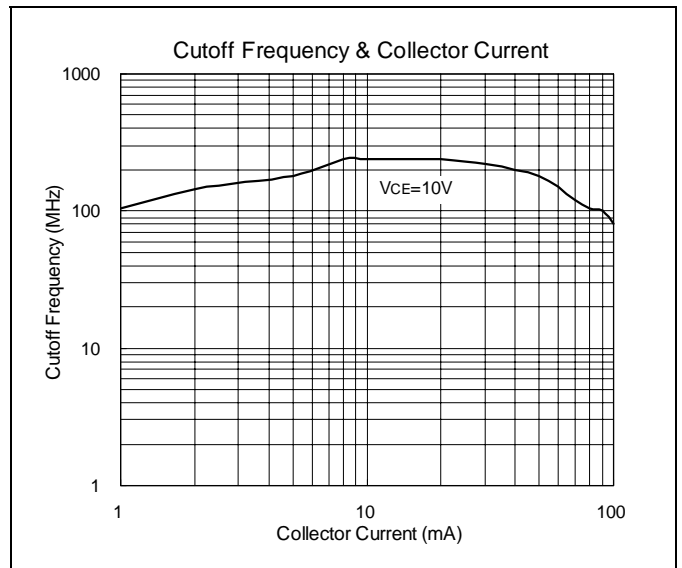
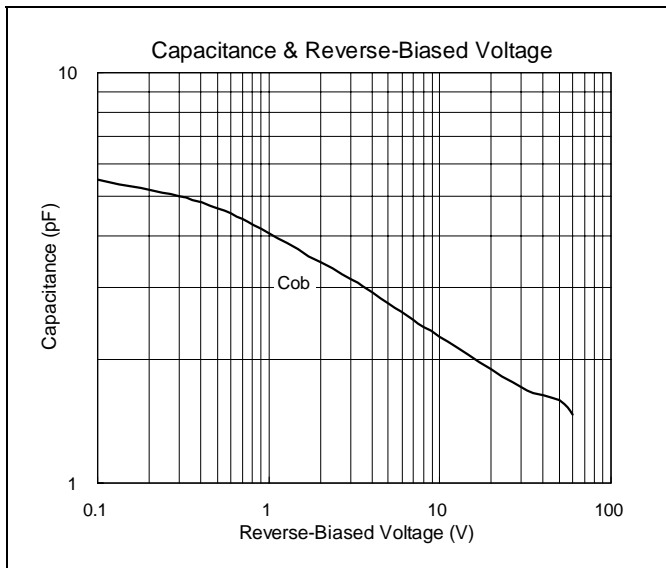
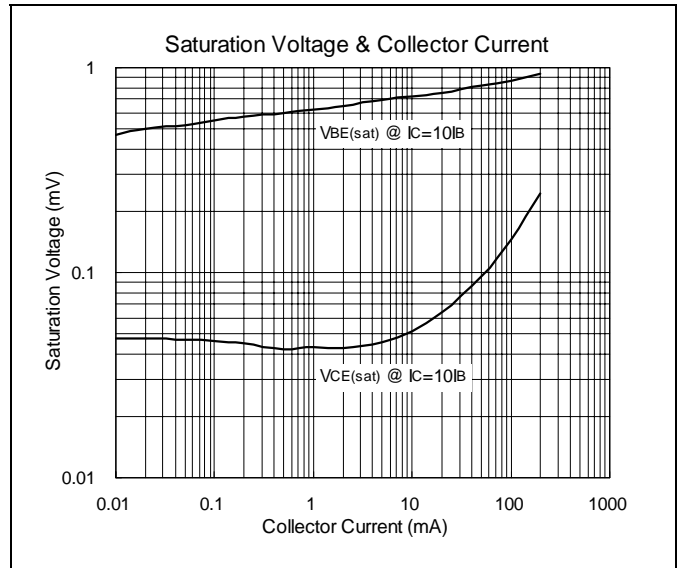
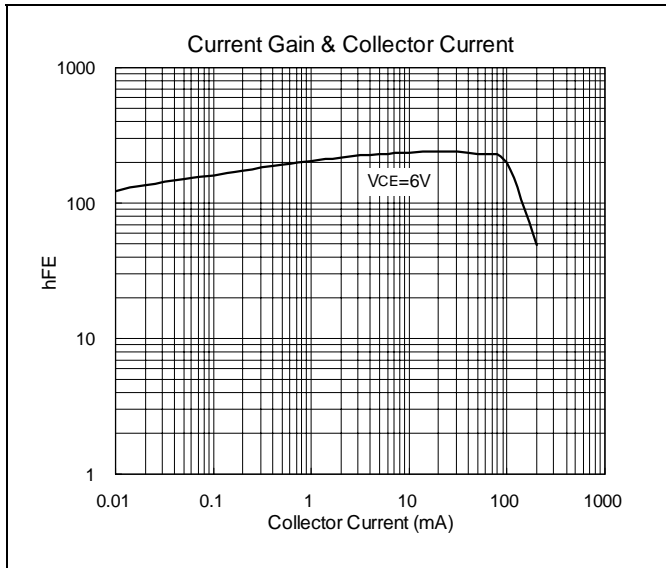
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	50	-	-	V	IC=100uA, IE=0
BVCEO	50	-	-	V	IC=1mA, IB=0
BVEBO	5	-	-	V	IE=10uA, IC=0
ICBO	-	-	100	nA	VCB=60V, IE=0
IEBO	-	-	100	nA	VEB=5V, IC=0
VCE(sat)	-	-	250	mV	IC=100mA, IB=10mA
VBE(sat)	-	-	1	V	IC=100mA, IB=10mA
hFE1	120	-	700		VCE=6V, IC=2mA
hFE2	25	-	-		VCE=6V, IC=150mA
fT	80	-	-	MHz	VCE=10V, IC=1mA, f=100MHz
Cob	-	-	3.5	pF	VCB=10V, f=1MHz, IE=0

### Classification of hFE1

Rank	Y	GR	BL
Range	120-240	200-400	350-700

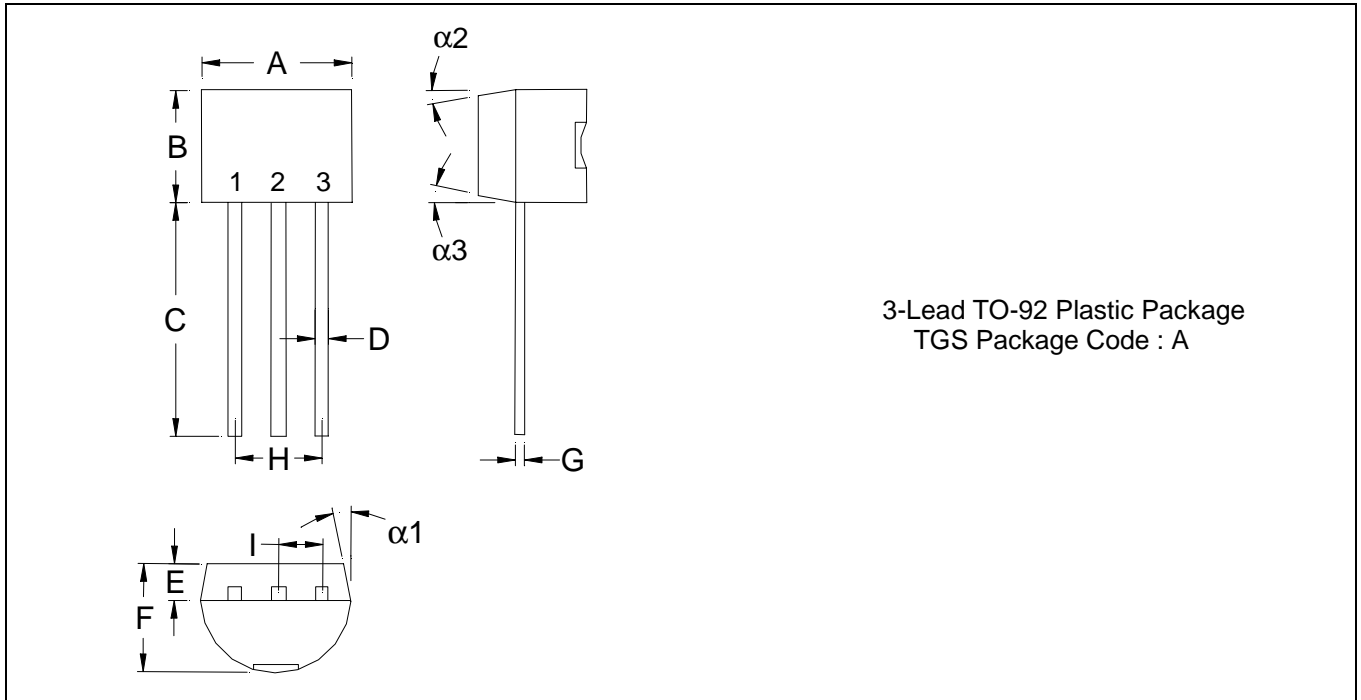


## Characteristics Curve





## TO-92 Dimension



\*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1704	0.1902	4.33	4.83	G	0.0142	0.0220	0.36	0.56
B	0.1704	0.1902	4.33	4.83	H	-	*0.1000	-	*2.54
C	0.5000	-	12.70	-	I	-	*0.0500	-	*1.27
D	0.0142	0.0220	0.36	0.56	$\alpha 1$	-	*5°	-	*5°
E	-	*0.0500	-	*1.27	$\alpha 2$	-	*2°	-	*2°
F	0.1323	0.1480	3.36	3.76	$\alpha 3$	-	*2°	-	*2°